

CYPRESS SEMICONDUCTOR

PRODUCT CHANGE NOTIFICATION

PCN:010008

DATE: May 7, 2001

Subject: Module, CY7C1345B-117AC SRAM Device Change affecting Module Devices CYM9260PM and CYM9261APM

To:

Description of change:

A change has been made to the SRAM populating the module devices listed above. The current CYM9260PM and CYM9261APM module devices are populated with CY7C1324-117AC SRAMs using the Ram 42D, a 0.35 μ technology. The CY7C1324-117AC will not be converted to Ram 52D-5R, a 0.25 μ process and will be obsoleted. Because of that, future module devices will be populated with CY7C1345B-117AC SRAMs using the Ram 52D-5R technology.

Because of the change to the SRAM, organizational changes have been made to the module devices. The current CYM9260PM used four (4) 128K x 18 100ld TQFPs and four (4) Clock signals. It was single-sided with four SRAMs per side. The revised module, the CYM9260CPM, will have two (2) 128K x 36 100ld TQFPs and one (1) clock signal. The number of decoupling caps was consolidated from thirty-five (35) to nineteen (19) and the 4.7K Ohm resistor was deleted.

The current CYM9261APM used eight (8) 128K x 18 100ld TQFPs. It was double-sided with four (4) SRAMs per side and four (4) clock signals. The revised module, the CYM9261CPM, will be single-sided with four (4) 128K x 36 100ld TQFPs and two (2) clock signals. The number of decoupling caps was consolidated from seventy (70) to thirty-five (35), the number of 0 Ohm resistors was decreased from seven (7) to four (4). The 4.7K Ohm resistor was deleted.

No change was made to the connector pin configuration of the module. The fit of the module into a system motherboard has not been affected.

Cypress part numbers affected:

CYM9260PM-50C, CYM9261APM-50C

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Customer part numbers affected:

15-2593-01 and 15-2594-01

Benefit of change:

This SRAM technology change will increase the number of good die per wafer, resulting in increased production capacity and improved deliveries.

Qualification status:

The CY7C1345B-117AC was qualified under SRAM QTP# 99503. A copy of the qualification report is included for review. Module samples built with the CY7C1345B-117AC SRAMs were characterized and compared to the datasheet. The characterization results at 25dgC and 80dgC are included for review.

Sample status:

Samples are available by contacting the local sales office.

Approximate Implementation Date:

Module product using the CY7C1345B-117AC will be available for production by the beginning of Q3/01.

End of Life Time (Die Change Only):

N/A

Response Required:

PCN Sent to:

Company:

For any additional information regarding this change, contact your local sales representative.

Sincerely,

Michael Burke
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CYM9260PM CHARACTERIZATION RESULTS USING THE CY7C1345B-117C SRAM

Characterization studies at 25dgC and 80dgC were performed on 2 CYM9260PM-50C modules using the CY7C1345B-117C SRAMs against the datasheet.

At 25dgC		SPECIFICATION		
PARAMETERS	Unit #1	Unit #2		
Tcdv	9.6 ns	9.6 ns	14 ns	
Vol	110.1 mV	110.1 mV	< 400 mV	
Voh	3.101 V	3.101 V	> 2.4 V	
Icc	8.584 mA	8.590 mA	1000 mA	
At 80dgC		SPECIFICATION		
PARAMETERS	Unit #1	Unit #2		
Tcdv	10.0 ns	10.0 ns	14 ns	
Vol	117.1 mV	120.1 mV	< 400 mV	
Voh	3.01 mV	3.111 V	> 2.4 V	
Icc	8.599 mA	8.715 mA	1000 mA	

ANALYSIS: In terms of speed, modules built with the CY7C1345 Ram 5 technology made the modular speed specification detailed in the datasheet.

DC parameters were within limits.

CONCLUSION: Based on the characterization data, the CY7C1345B-117C units met the CYM9260PM datasheet specification.

CYM9261PM CHARACTERIZATION RESULTS USING THE CY7C1345B-117C SRAM

Characterization studies at 25dgC and 80dgC were performed on 2 CYM9261APM-50C modules using the CY7C1345B-117C SRAMs against the datasheet.

At 25dgC	Unit #1	Unit #2	SPECIFICATION
PARAMETERS			
Tcdv	9.6 ns	9.6 ns	14 ns
Vol	105.9 mV	103.1 mV	< 400 mV
Voh	3.101 V	3.101 V	> 2.4 V
Icc	99.93 mA	100.5 mA	1000 mA

At 80dgC	Unit #1	Unit #2	SPECIFICATION
PARAMETERS			
Tcdv	9.8 ns	9.8 ns	14 ns
Vol	108.1 mV	111.9 mV	< 400 mV
Voh	3.121 V	3.111 V	> 2.4 V
Icc	100.3 mA	98.12 mA	1000 mA

ANALYSIS: In terms of speed, modules built with the CY7C1345 Ram 5 technology made the modular speed specification detailed in the datasheet.

DC parameters were within limits.

CONCLUSION: Based on the characterization data, the CY7C1345B-117C units met the CYM9261APM datasheet specification.